

Amendments to the Specification:

Please replace the paragraph beginning at page 17, line 2, with the following amended paragraph:

A second semiconductor film 206 is formed next on the barrier layer 205. (See Fig. 2C.) The second semiconductor film 206 contains an inert gas element. [[A]] The semiconductor film 206 having an amorphous structure may be formed, and [[a]] the semiconductor film 206 having a crystalline structure may also be formed. It is preferable to include oxygen in the second semiconductor film 206 (at a concentration measured by SIMS analysis equal to or greater than $5 \times 10^{18} / \text{cm}^3$, preferably equal to or greater than $1 \times 10^{19} / \text{cm}^3$) to increase gettering efficiency.